



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
SWITCHING DIODE ARRAY**

VOLTAGE 80 Volts CURRENT 250 mAmpere

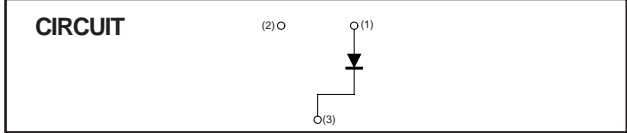
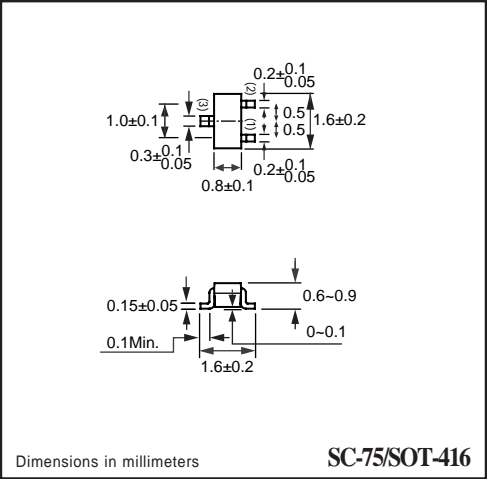
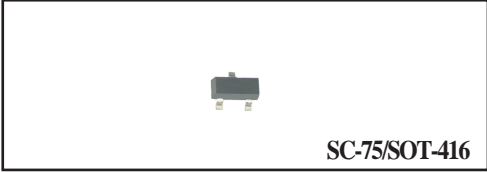
MMBD4448TGP

APPLICATION
* Fast high speed switching

FEATURE
* Small surface mounting type. (SC-75/SOT-416)
* High speed. ($T_{RR}=4.0nSec$ Max.)
* Fast Switching Speed.
* Ultra-Small Surface Mount Package.
* For General Purpose Switching Applications.
* High Conductance.

CONSTRUCTION
* Silicon epitaxial planar

MARKING
* TJ



MAXIMUM RATINGS (At $T_A = 25^{\circ}C$ unless otherwise noted)

RATINGS	SYMBOL	MMBD4448TGP	UNITS
Maximum Non-Repetitive Peak Reverse Voltage	V_{RM}	100	Volts
Maximum Repetitive Peak Reverse Voltage Maximum Working Peak Reverse Voltage Maximum DC Blocking Voltage	V_{RRM} V_{RWM} V_{DC}	80	Volts
Maximum RMS Voltage	V_{RMS}	57	Volts
Maximum Average Forward Rectified Current	I_O	250	mAmps
Repetitive Peak Forward Current	I_{FRM}	500	mAmps
Peak Forward Surge Current at 1uSec.	@ 1Sec	2.0	Amps
	@ 1.0uSec	4.0	
Total Capacitance	C_T	3.5	pF
Maximum Reverse Recovery Time	t_{rr}	4.0	nSec
Maximum Thermal Resistance	$R_{\theta JA}$	625	$^{\circ}C/W$
Maximum Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (At $T_A = 25^{\circ}C$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	MMBD4448TGP	UNITS
Maximum Instantaneous Forward Voltage @ $I_F = 5.0$ mA @ $I_F = 100$ mA	V_F	0.72 1.0	Volts
Maximum Average Reverse Current (Note 1) $V_R = 20V$ @ $T_J = 25^{\circ}C$ $V_R = 75V$ @ $T_J = 150^{\circ}C$ $V_R = 25V$ @ $T_J = 150^{\circ}C$	I_R	25nA 50 30	uAmps

NOTES : 1. Short duration test pulse used to minimize self-heating effect.

2004-10

RATING CHARACTERISTIC CURVES (MMBD4448TGP)

FIG. 1 - FORWARD CHARACTERISTICS

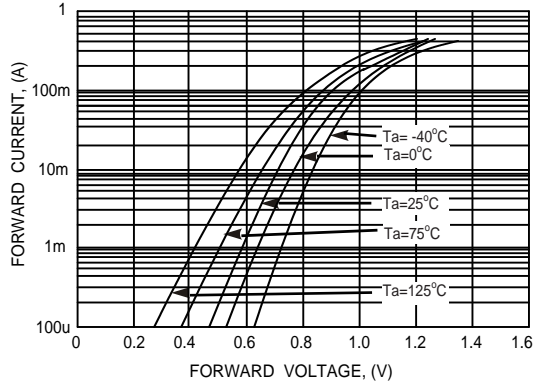


FIG. 2 - REVERSE CHARACTERISTICS

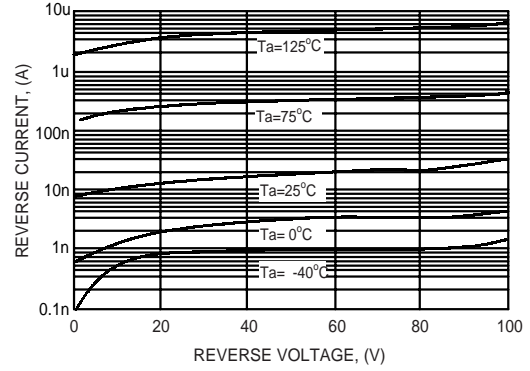


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

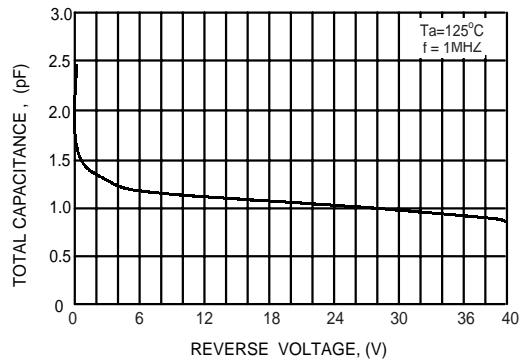


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

